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Vishay Semiconductors

Thyristor Surface Mount Phase Control SCR, 16 A



PRODUCT SUMMARY							
Package	TO-263AB (D ² PAK)						
Diode variation	Single SCR						
I _{T(AV)}	10 A						
V_{DRM}/V_{RRM}	1600 V						
V_{TM}	1.4 V						
I _{GT}	60 mA						
T_J	-40 °C to 125 °C						

FEATURES

 Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C



 Designed and qualified according JEDEC®-JESD 47

 Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

APPLICATIONS

- · Input rectification (soft start)
- Vishay input diodes, switches and output rectifiers which are in identical package outlines

DESCRIPTION

The VS-16TTS16SPbF high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS								
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS								
NEMA FR-4 or G-10 glass fabric-based epoxy with 4 oz. (140 µm) copper	2.5	3.5						
Aluminum IMS, R _{thCA} = 15 °C/W	6.3	9.5	A					
Aluminum IMS with heatsink, R _{thCA} = 5 °C/W	14.0	18.5						

Note

• $T_A = 55$ °C, $T_J = 125$ °C, footprint 300 mm²

MAJOR RATINGS AND CHARACTERISTICS								
SYMBOL	CHARACTERISTICS	VALUES	UNITS					
I _{T(AV)}	Sinusoidal waveform	10	^					
I _{RMS}		16	A					
V _{RRM} /V _{DRM}		1600	V					
I _{TSM}		200	А					
V _T	10 A, T _J = 25 °C	1.4	V					
dV/dt		500	V/µs					
dl/dt		150	A/µs					
T _J		-40 to 125	°C					

VOLTAGE RATINGS									
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} /I _{DRM} AT 125 °C mA						
VS-16TTS16SPbF	1600	1600	10						



ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL		TEST CONDITIONS	VAL	UNITS				
PARAMETER	STIVIBUL		1EST CONDITIONS	TYP.	UNITS				
Maximum average on-state current	I _{T(AV)}	T _C = 93 °C, 18	0° conduction, half sine wave	1	0				
Maximum RMS on-state current	I _{RMS}			1	6	Α			
Maximum peak, one-cycle,	ı	10 ms sine pu	lse, rated V _{RRM} applied	17	70	_ ^			
non-repetitive surge current	I _{TSM}	10 ms sine pu	lse, no voltage reapplied	20	00				
Maximum I ² t for fusing	I ² t	10 ms sine pu	lse, rated V _{RRM} applied	144		A ² s			
Maximum 1-t for fusing	I-t	10 ms sine pu	lse, no voltage reapplied	200		A-S			
Maximum I ² √t for fusing	I ² √t	t = 0.1 ms to 1	t = 0.1 ms to 10 ms, no voltage reapplied						
Maximum on-state voltage drop	V_{TM}	10 A, T _J = 25 °	10 A, T _J = 25 °C			V			
On-state slope resistance	r _t	T 105 °C		24.0		mΩ			
Threshold voltage	V _{T(TO)}	T _J = 125 °C		1.1		V			
Maximum various and direct lanks as assured	1 /1	T _J = 25 °C	V Dated V A/	0	.5				
Maximum reverse and direct leakage current	I_{RM}/I_{DM}	T _J = 125 °C	$V_R = Rated V_{RRM}/V_{DRM}$		0				
Holding current	I _H	Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 °C			150	mA			
Maximum latching current	ΙL	Anode supply	200						
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J \text{ max. li}$	$T_J = T_J$ max. linear to 80 % $V_{DRM} = Rg - k = Open$			V/µs			
Maximum rate of rise of turned-on current	dI/dt				50	A/µs			

TRIGGERING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum peak gate power	P_{GM}		8.0	W				
Maximum average gate power	P _{G(AV)}		2.0	VV				
Maximum peak positive gate current	+ I _{GM}		1.5	А				
Maximum peak negative gate voltage	- V _{GM}		10	V				
		Anode supply = 6 V, resistive load, T _J = - 10 °C	90	mA				
Maximum required DC gate current to trigger	I _{GT}	Anode supply = 6 V, resistive load, T _J = 25 °C	60					
		Anode supply = 6 V, resistive load, T _J = 125 °C	35					
		Anode supply = 6 V, resistive load, T _J = - 10 °C	3.0					
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, T _J = 25 °C	2.0	, I				
voltage to trigger		Anode supply = 6 V, resistive load, T _J = 125 °C	1.0	V				
Maximum DC gate voltage not to trigger	V_{GD}	T 105 °C V Detectively	0.25					
Maximum DC gate current not to trigger	I _{GD}	T _J = 125 °C, V _{DRM} = Rated value	2.0	mA				

SWITCHING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9	1				
Typical reverse recovery time	t _{rr}	T _{.I} = 125 °C	4	μs				
Typical turn-off time	t _q		110					

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum junction and storage temperature range	T _J , T _{Stg}		- 40 to 125	°C			
Soldering temperature	T _S	For 10 s (1.6 mm from case)	260				
Maximum thermal resistance, junction to case	R _{thJC} DC operation		1.3	°C/W			
Typical thermal resistance, junction to ambient	R _{thJA}	PCB mount (1)	40				
Approximate weight			2	g			
Approximate weight			0.07	OZ.			
Marking device		Case style D ² PAK (SMD-220)	16TTS	16S			

Note

⁽¹⁾ When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 μm) copper 40 °C/W. For recommended footprint and soldering techniques refer to application note #AN-994.

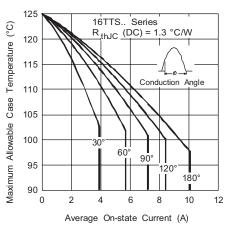


Fig. 1 - Current Rating Characteristics

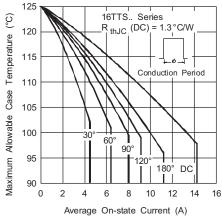


Fig. 2 - Current Rating Characteristics

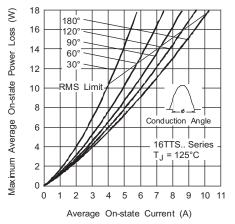


Fig. 3 - On-State Power Loss Characteristics

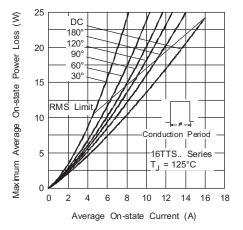


Fig. 4 - On-State Power Loss Characteristics



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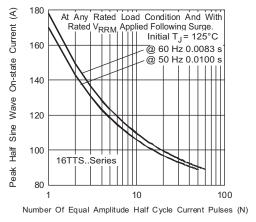


Fig. 5 - Maximum Non-Repetitive Surge Current

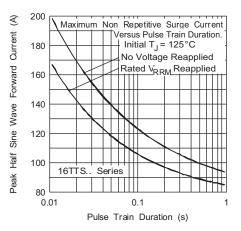


Fig. 6 - Maximum Non-Repetitive Surge Current

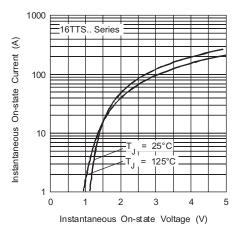


Fig. 7 - On-State Voltage Drop Characteristics

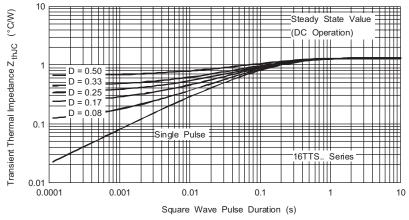


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

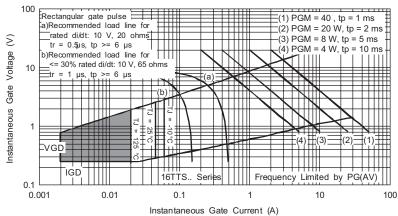
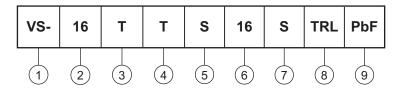


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code



- 1 Vishay Semiconductors product
- 2 Current rating
- Circuit configuration:

T = single thyristor

4 - Package:

T = TO-220AC

5 - Type of silicon:

S = standard recovery rectifier

- 6 Voltage rating: Voltage code x 100 = V_{RRM} (16 = 1600 V)
- 7 S = TO-220 D²PAK (SMD-220) version
- 8 • None = tube
 - TRL = tape and reel (left oriented)
 - TRR = tape and reel (right oriented)
- 9 PbF = lead (Pb)-free

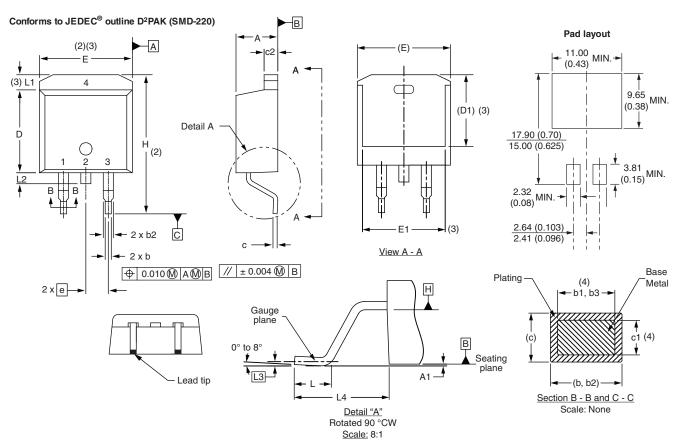
ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-16TTS16SPbF	50	1000	Antistatic plastic tubes					
VS-16TTS16STRRPbF	800	800	13" diameter reel					
VS-16TTS16STRLPbF	800	800	13" diameter reel					

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95046				
Part marking information	www.vishay.com/doc?95054				
Packaging information	www.vishay.com/doc?95032				



D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIM	ETERS	INC	HES	NOTES	
STIMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100) BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC® outline TO-263AB



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